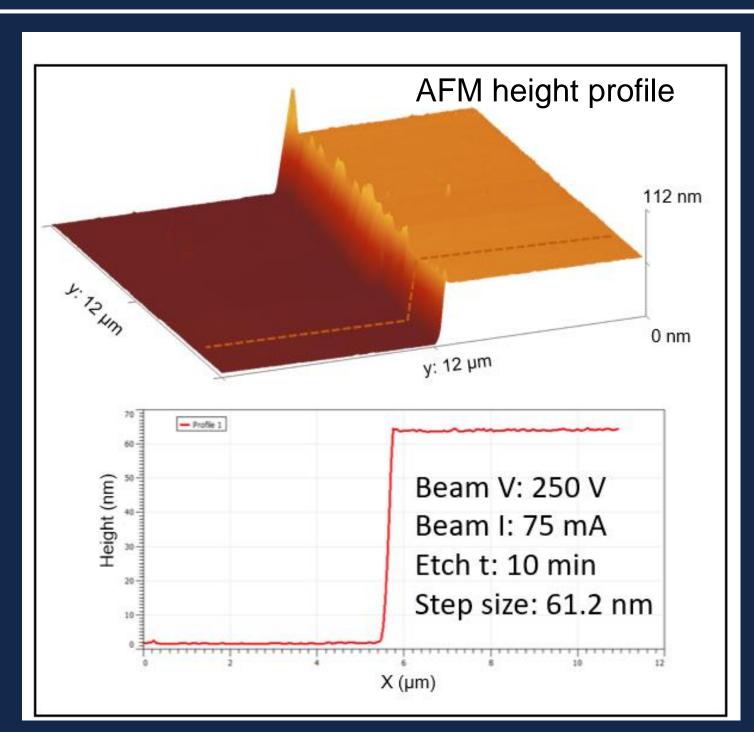
J[**LLINOIS** Materials Research Laboratory **GRAINGER COLLEGE OF ENGINEERING**



A sharp step on the silicon ightarrow

Commonwealth Ion Milling and Thermal Evaporator MRL Microfabrication Lab MRL 334

- Integrated ion milling ightarrowand thermal evaporation capability
- Dedicated to the deposition of:

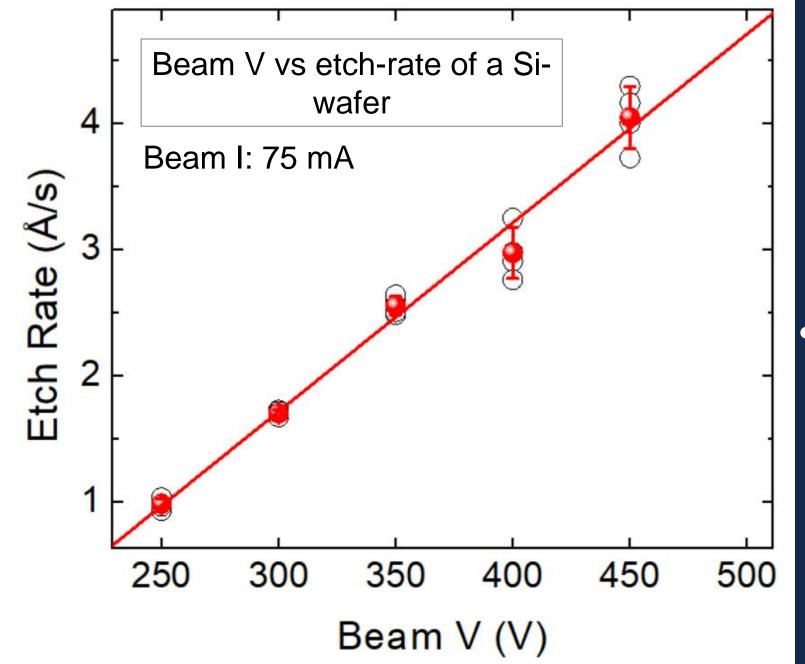
MMONWEAT

✤ Cu ✤ Pb Sn 🛠 ✤ In ✤ Sb ✤ Au ✤ Cr st Ag ✤ Ni ✤ Fe 💠 Ti $\bigstar MoO_3$

and more.

surface etched using Commonwealth ion mill (up)

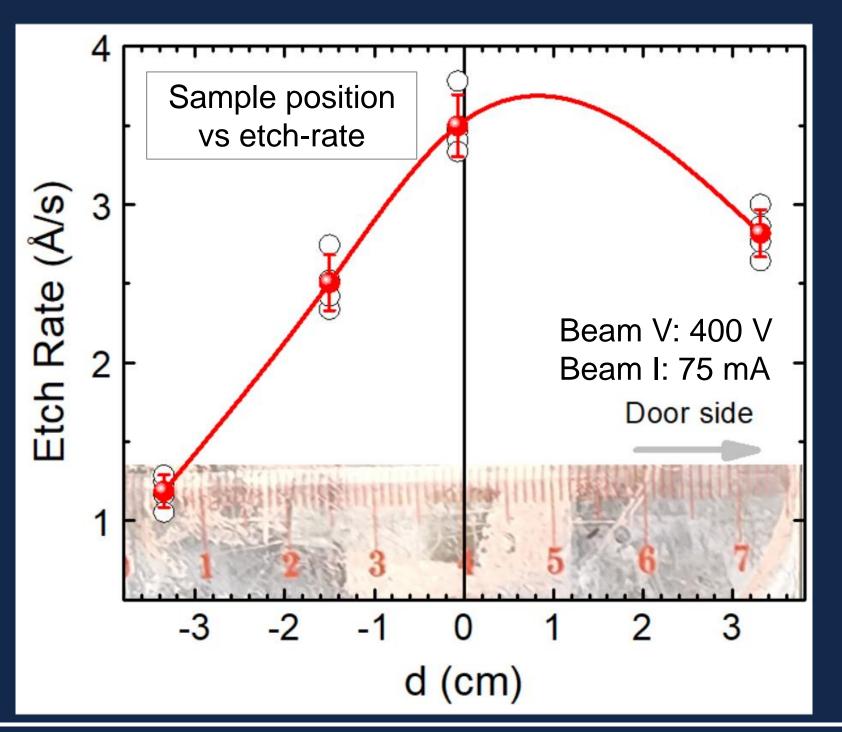


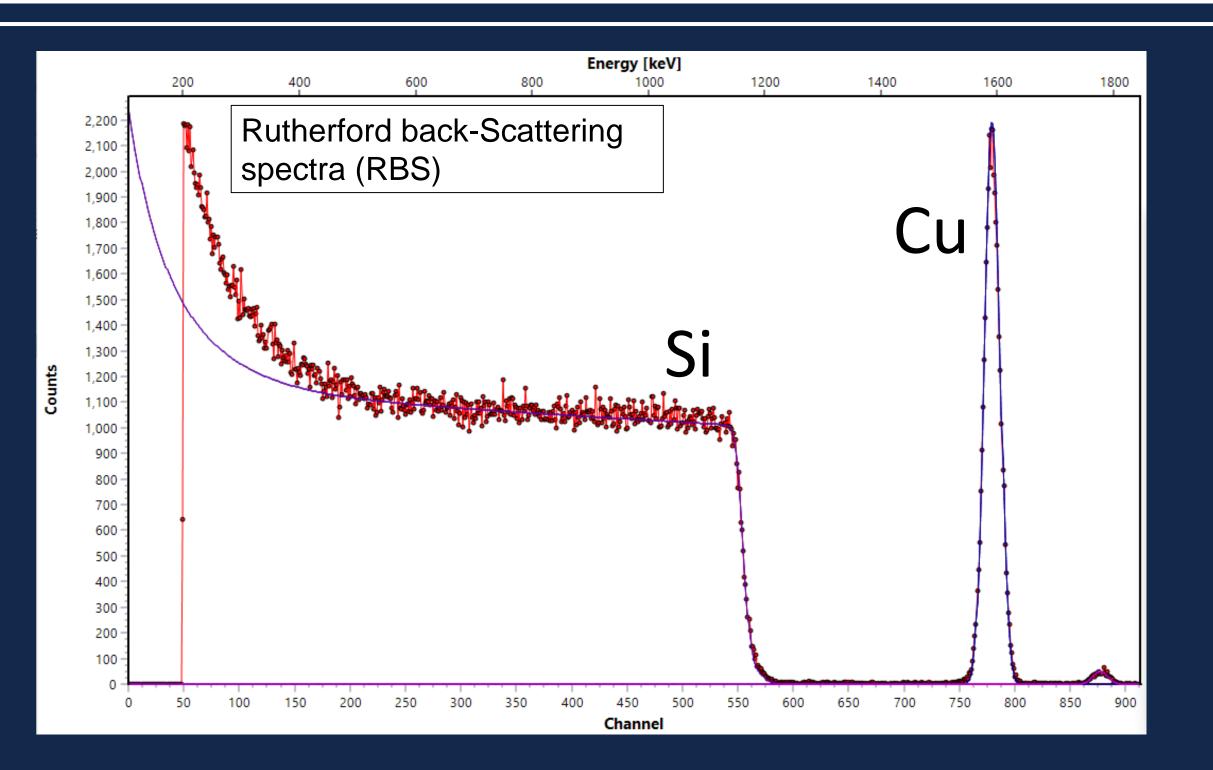


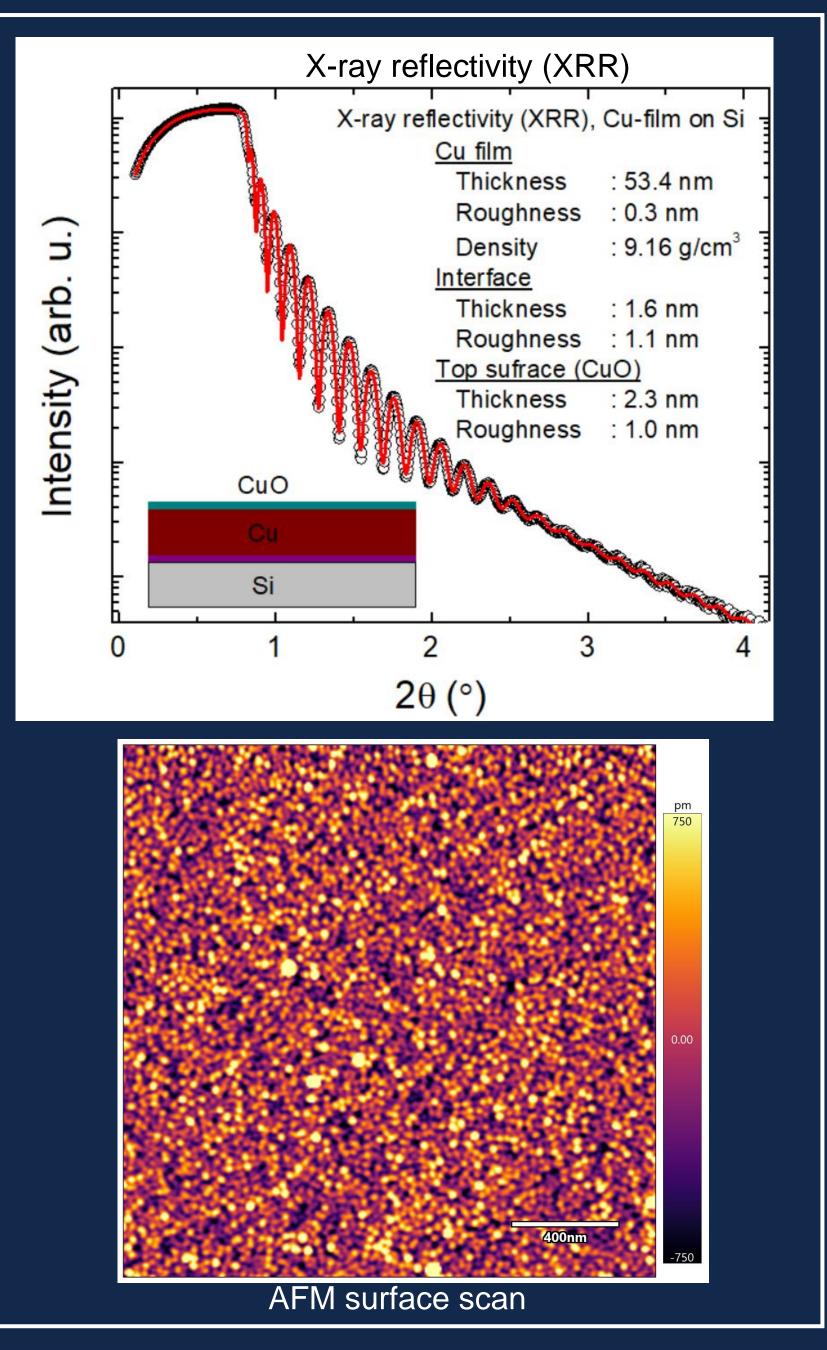
Highly focused ulletion beam near the center of the sample stage

MILLATRON

Beam voltage (V) and/or beam current (I) can be varied to obtain the desired etchrate







- Rutherford back-scattering (RBS) spectrum measured • from a 15 nm Cu-film deposited on a Si wafer using the Commonwealth Thermal Evaporator (up)
- X-ray reflectivity (XRR) measured from a 53.4 nm Cu-film ulletgrown on Si wafer with a GenX simulation (top right)
- Atomic force microscopy (AFM) surface scan of an ightarrowatomically flat Cu-film grown on Si-wafer (RMS) roughness: 380 pm) (bottom right)

For more information, please visit *mrl.illinois.edu*.